

This cross-sectional view shows a semiconductor device with a substrate 11 and a top layer 88. A central region 13 contains a series of stacked layers: 14, 16, 17, 21, 26, 28, 29, 32, 34, 36, 37, 41, 49, 59, 61, 63, 66, and 84. The layers are separated by interfaces 19 and 20. A dimension line 31 indicates the thickness of the top layer 88. A dimension line 36 indicates the thickness of the layer 26. A dimension line 37 indicates the thickness of the layer 37. A dimension line 41 indicates the thickness of the layer 41. A dimension line 49 indicates the thickness of the layer 49. A dimension line 59 indicates the thickness of the layer 59. A dimension line 61 indicates the thickness of the layer 61. A dimension line 63 indicates the thickness of the layer 63. A dimension line 66 indicates the thickness of the layer 66. A dimension line 84 indicates the thickness of the layer 84. A dimension line 87 indicates the thickness of the layer 87. A dimension line 88 indicates the thickness of the layer 88.

FIG. 1



TITLE: VERTICAL COMPOUND SEMICONDUCTOR
FIELD EFFECT TRANSISTOR STRUCTURE
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2/4

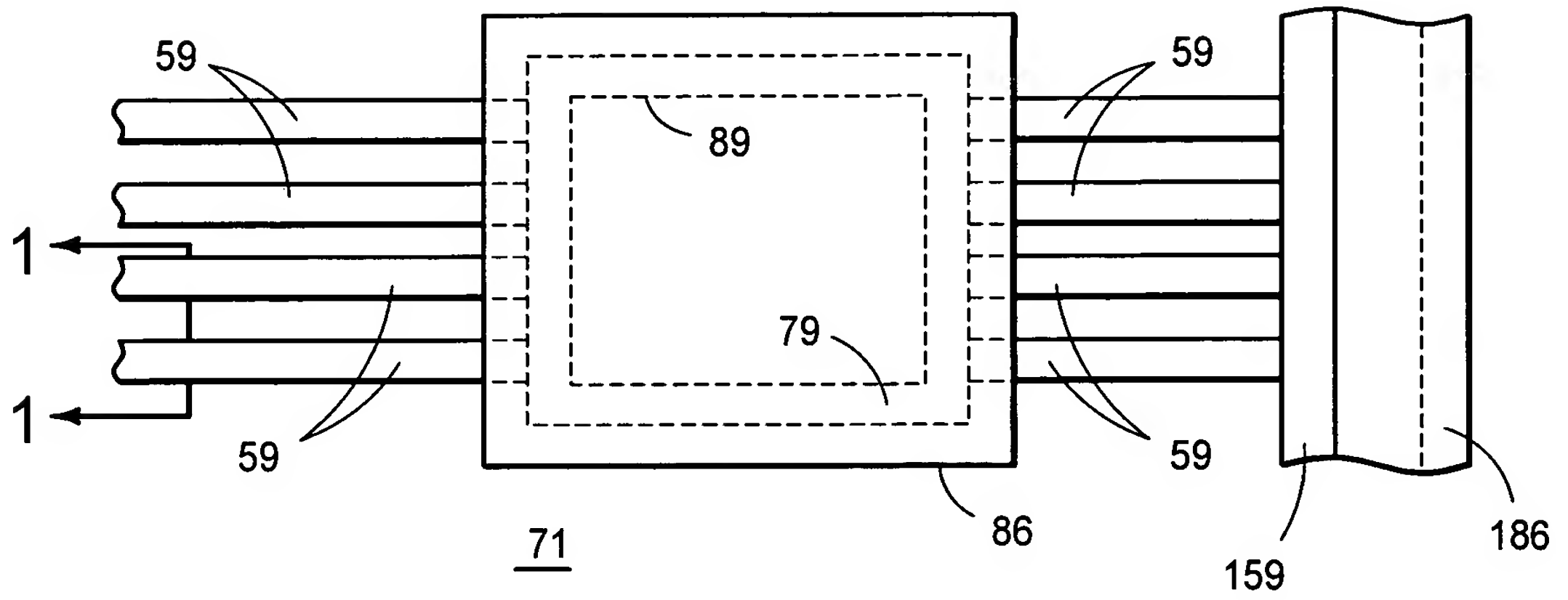


FIG. 2

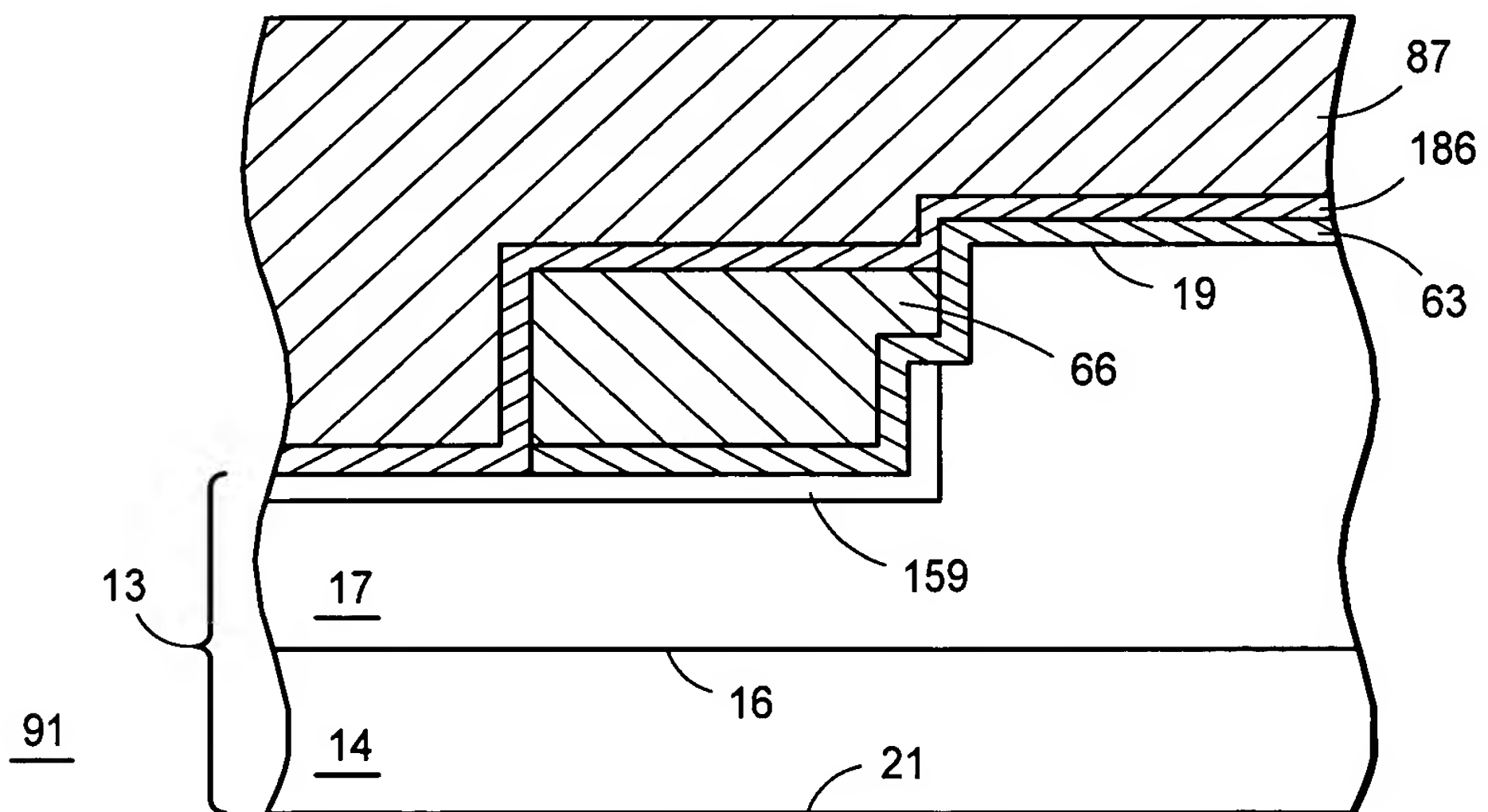


FIG. 3



3/4

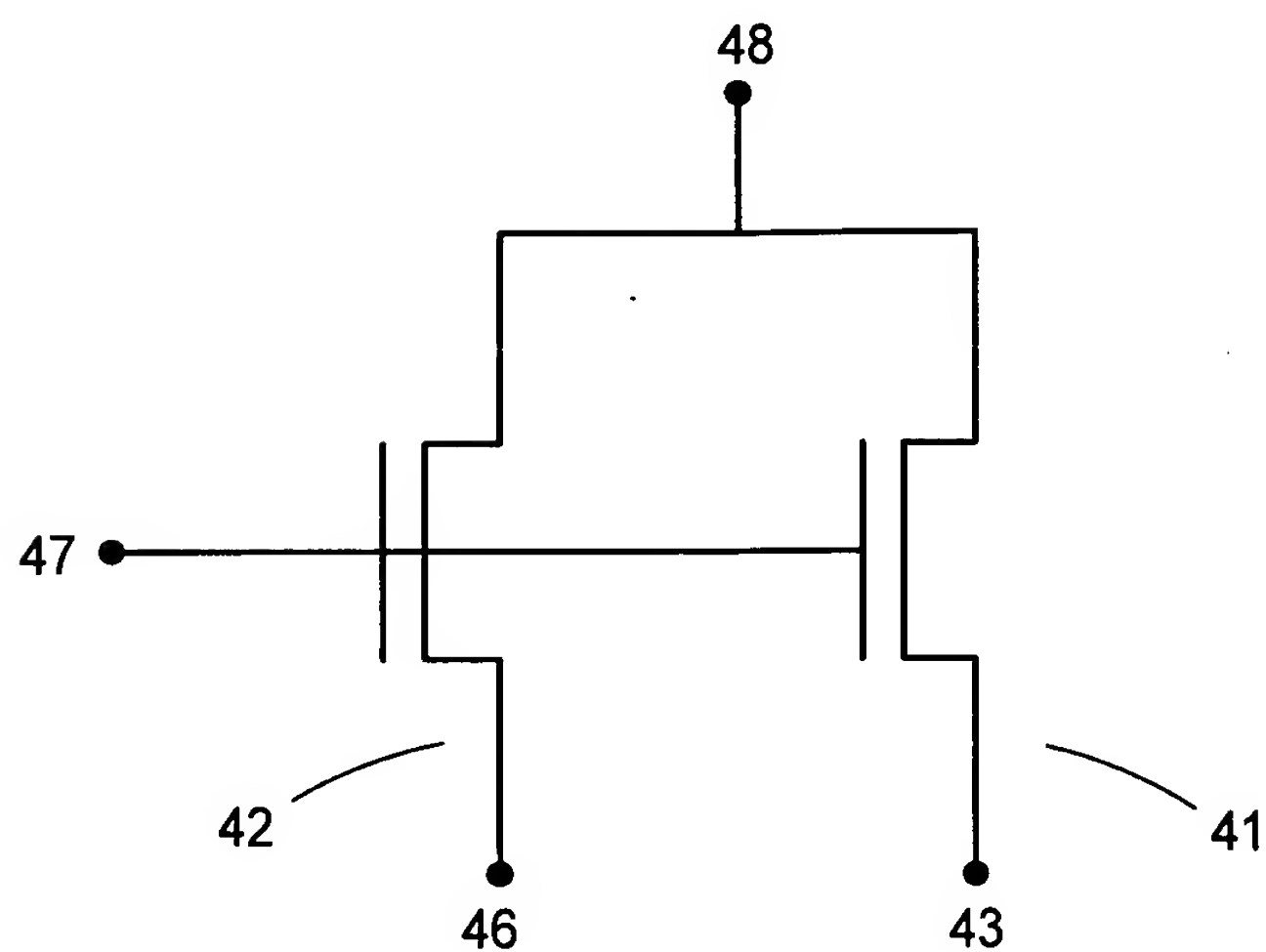


FIG. 4

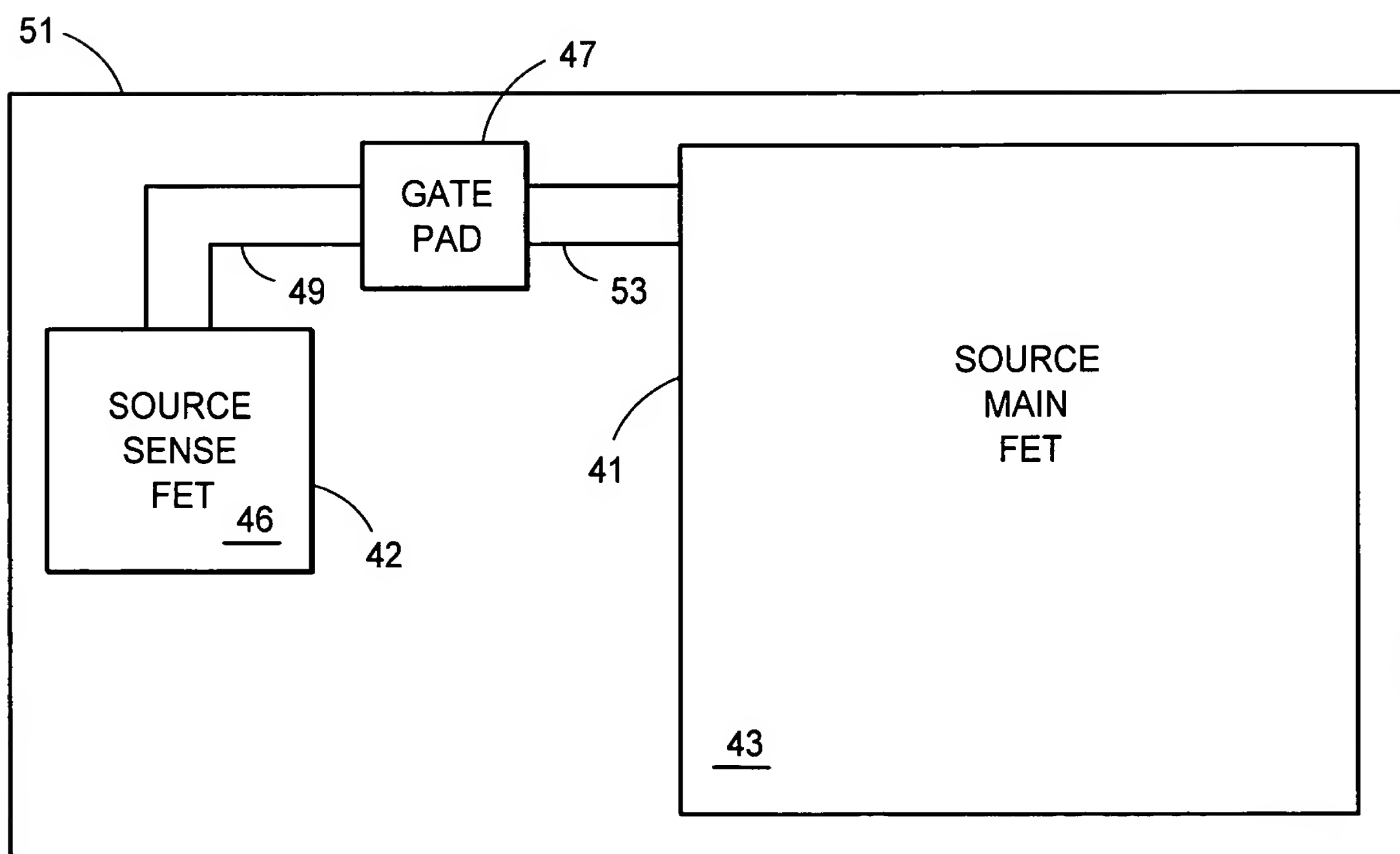
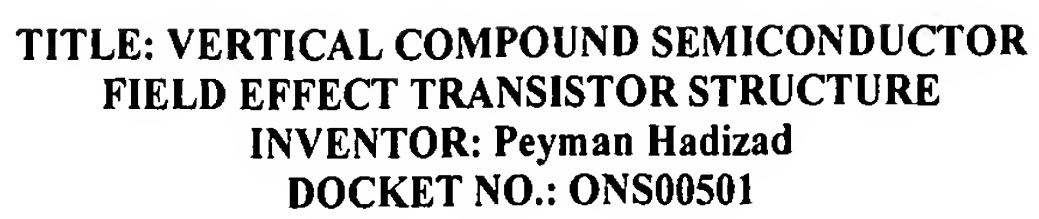


FIG. 5

66
G.
F.